

OPA5723YGO

Yellow Green LED Chip

Ultra Bright

GaAs/AlGaInP

1. Material Substrate GaAs (N Type)
Epitaxial Layer AlGaInP (P/N Type)

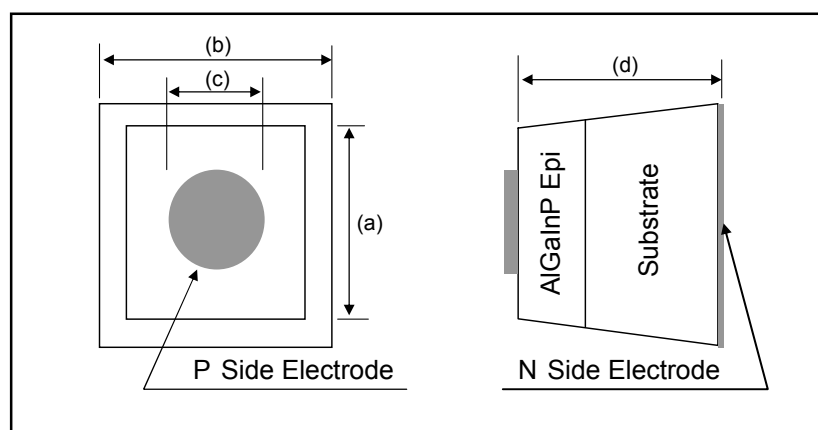
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		2.2	2.4	V	IF=20mA
Reverse Current	I_R			100	uA	VR=5V
Brightness	I_v	20	35		mcd	IF=20mA
Wavelength	λ_d		574		nm	IF=20mA
	$\Delta\lambda$		20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

4. Mechanical Data (a) Emission Area ----- 8mil x 8mil
(b) Bottom Area ----- 9mil x 9mil
(c) Bonding Pad ----- 100um
(d) Chip Thickness ----- 7.0mil

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